



CHENMKO ENTERPRISE CO.,LTD

Lead free devices

**SMALL FLAT
NPN Epitaxial Transistor**

VOLTAGE 20 Volts CURRENT 5 Amperes

2SD2098PPT

APPLICATION

- * Power driver and Strobe Flash .

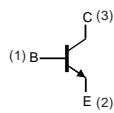
FEATURE

- * Small flat package. (DPAK)
- * Low saturation voltage $V_{CE(sat)}=0.25V$ (Typ.)($I_c/I_B=4A/0.1A$)
- * High saturation current capability.

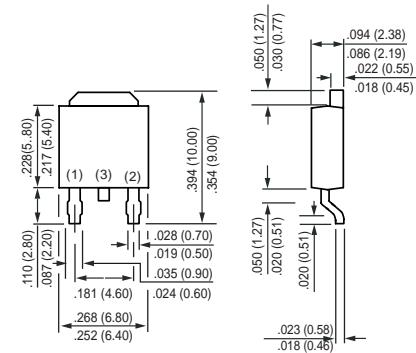
CONSTRUCTION

- * NPN Cilicon Transistor

CIRCUIT



DPAK



Dimensions in inches and (millimeters)

DPAK

MAXIMUM RATINGS (At $T_A = 25^\circ\text{C}$ unless otherwise noted)

RATINGS	CONDITION	SYMBOL	MIN.	MAX.	UNITS
Collector - Base Voltage	Open Emitter	V_{CBO}	-	50	Volts
Collector - Emitter Voltage	Open Base	V_{CEO}	-	20	Volts
Emitter - Base Voltage	Open Collector	V_{EBO}	-	6	Volts
Collector Current DC		I_C	-	5	Amps
Peak Collector Current		I_{CM}	-	10	Amps
Peak Base Current		I_{BM}	-	0.5	Amps
Total Power Dissipation	$T_A \leq 25^\circ\text{C}$; Note 1	P_{TOT}	-	1.0	W
Storage Temperature		T_{STG}	-55	+150	$^\circ\text{C}$
Junction Temperature		T_J	-	+150	$^\circ\text{C}$
Operating Ambient Temperature		T_{AMB}	-55	+150	$^\circ\text{C}$

Note

1. Transistor mounted on ceramic substrate by 40mmX40mmx0.7mm.
2. Measured at Pulse Width 300 us, Duty Cycle 2%.

2006-01

RATING CHARACTERISTIC CURVES (2SD2098PPT)

CHARACTERISTICS (At TA = 25°C unless otherwise noted)

PARAMETERS	CONDITION	SYMBOL	MIN.	TYPE	MAX.	UNITS
Collector Cut-off Current	I _E =0; V _{CB} =40V	I _{CBO}	-	-	0.5	uA
Emitter Cut-off Current	I _C =0; V _{EB} =5V	I _{CEO}	-	-	0.5	uA
DC Current Gain	V _{CE} =2V; Note 1 I _C =0.5A	h _{FE}	230	-	600	
Collector-Emitter Saturation Voltage	I _C =3A; I _B =0.1A	V _{CEsat}	-	0.25	0.8	Volts
Base-Emitter Saturation Voltage	I _C =4A; I _B =0.1A	V _{BEsat}	-	1.0	2.0	Volts
Collector Capacitance	I _E =I _B =0; V _{CB} =10V; f=1MHz	C _c	-	30	-	pF
Transition Frequency	I _C =-0.05A; V _{CE} =6.0V; f=100MHz	f _T	-	150	-	MHz

Note :

1. Pulse test: t_p ≤ 300uSec; δ ≤ 0.02.

RATING CHARACTERISTIC CURVES (2SD2098PPT)

Fig.1 Grounded emitter propagation characteristics

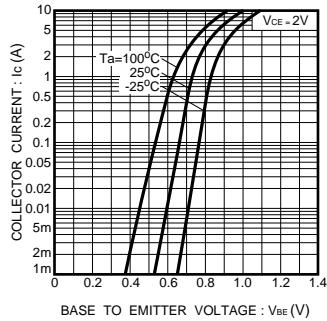


Fig.2 Grounded emitter output characteristics

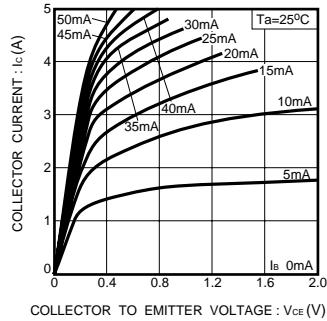


Fig.3 DC current gain vs. collector current (I)

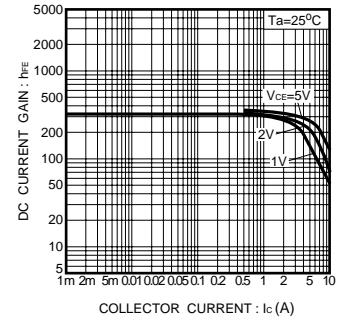


Fig.4 DC current gain vs. collector current (II)

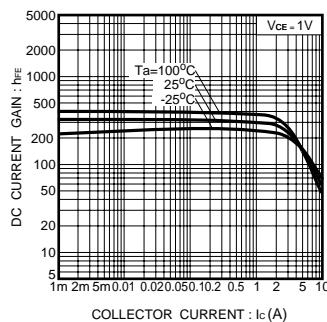


Fig.5 DC current gain vs. collector current (III)

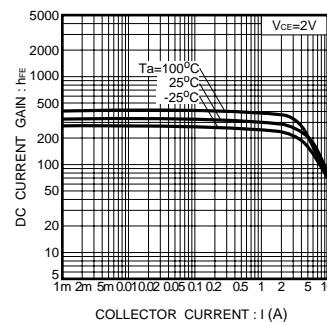


Fig.6 Collector-emitter saturation voltage vs. collector current (I)

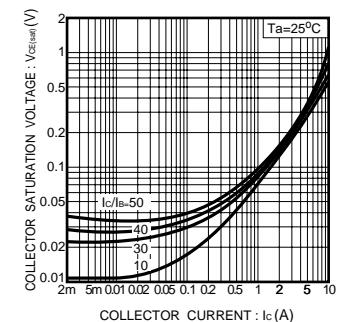


Fig.7 Collector-emitter saturation voltage vs. collector current (V)

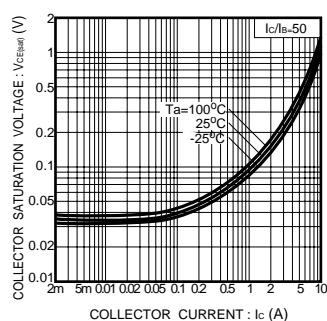


Fig.8 Gain bandwidth product vs. emitter current

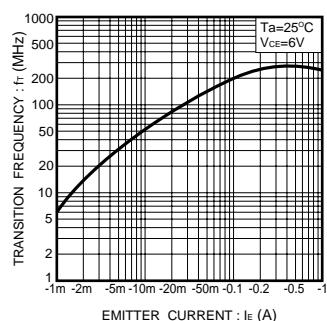


Fig.9 Collector output capacitance vs. collector-base voltage
Emitter input capacitance vs. emitter-base voltage

